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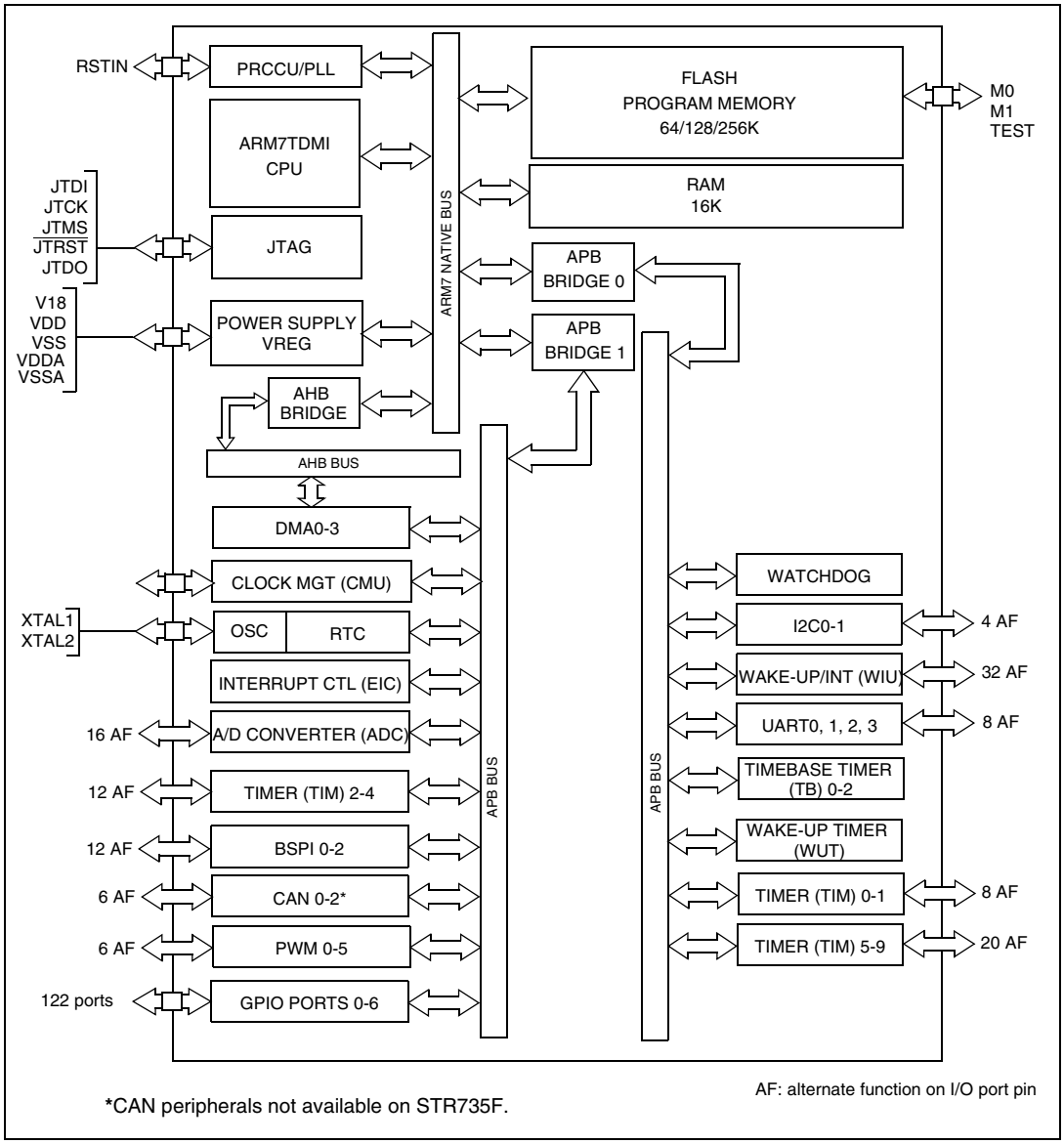
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	72
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str736fv1t6

3 Block diagram

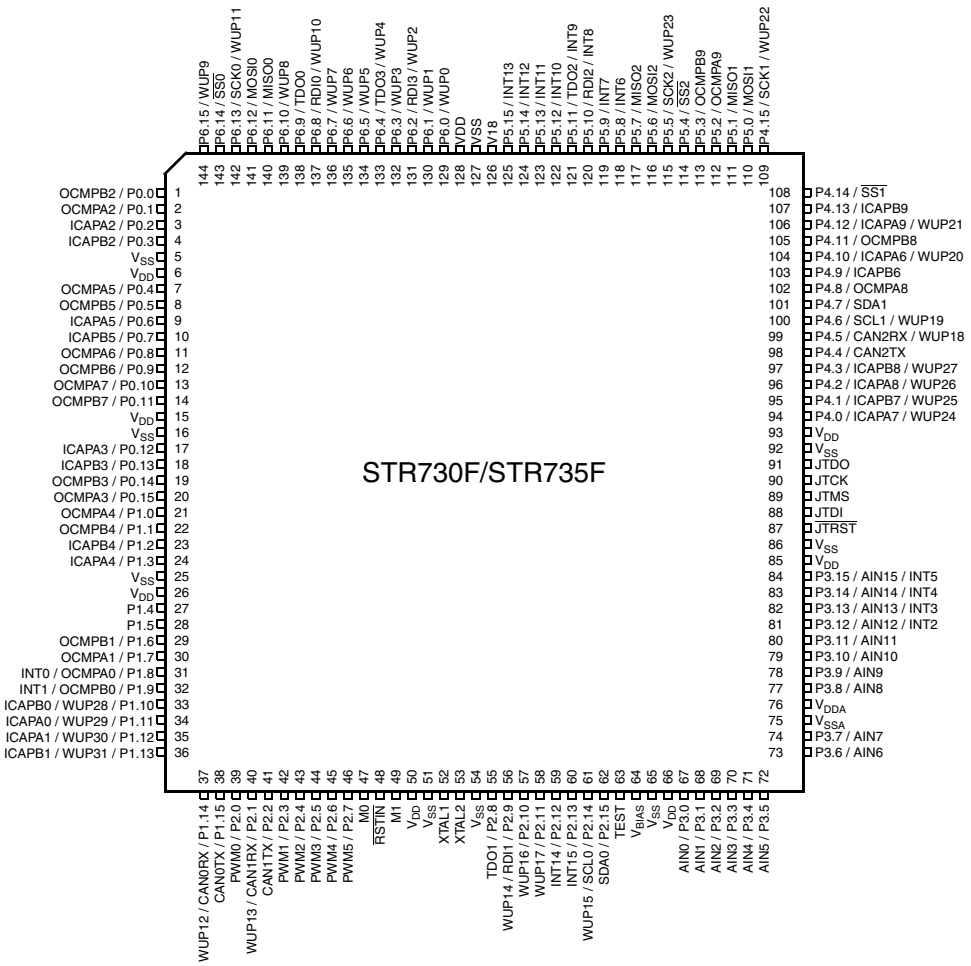
Figure 1. STR730F/STR735F block diagram



3.2 Pin description

3.2.1 STR730F/STR735F (TQFP144)

Figure 3. STR730F/STR735F pin configuration (top view)



Note: CAN alternate functions not available on STR735F.

3.2.2 STR730F/STR735F (LFBGA144)

Table 3. STR730F/STR735F LFBGA ball connections

Ball	Name	Ball	Name	Ball	Name	Ball	Name
A1	P0.0 / OCMPB2	B1	P0.4 / OCMPA5	C1	P0.5 / OCMPB5	D1	V_{SS}
A2	P6.10 / WUP8	B2	P0.1 / OCMPA2	C2	P0.2 / ICAPA2	D2	V_{DD}
A3	P6.9 / TDO0	B3	P6.15 / WUP9	C3	P0.3 / ICAPB2	D3	P0.6 / ICAPA5
A4	P6.12 / MOSI0	B4	P6.13 / SCKO / WUP11	C4	P6.14 / SSO	D4	P0.7 /ICAPB5
A5	P6.6 / WUP6	B5	P6.7 / WUP7	C5	P6.8 / RDI0 / WUP10	D5	P6.11 / MISO0
A6	V_{18}	B6	P6.2 / WUP2 / RDI3	C6	P6.3 / WUP3	D6	P6.4 / WUP4 /TDO3
A7	P5.15 / INT13	B7	P5.14 / INT12	C7	V_{SS}	D7	VDD
A8	P5.8 / INT6	B8	P5.9 / INT7	C8	P5.10 / INT8 / RDI2	D8	P5.12 / INT10
A9	P5.2 / OCMPA9	B9	P5.3 / OCMPB9	C9	P5.4 / SS2	D9	P5.5 / SCK2 / WUP23
A10	P5.7 / MISO2	B10	P5.0 / MOSI1	C10	P5.1 / MISO1	D10	P4.13 / ICAPB9
A11	P5.6 / MOSI2	B11	P4.15 / SCK1 / WUP22	C11	P4.14 / SS1	D11	P4.12 / ICAPA9 / WUP21
A12	P5.11 / TDO2 / INT9	B12	P4.8 / OCMPA8	C12	P4.7 / SDA1	D12	P4.11 / OCMPB8
E1	P0.8 / OCMPA6	F1	V_{DD}	G1	V_{SS}	H1	V_{DD}
E2	P0.9 / OCMPB6	F2	P0.13 / ICAPB3	G2	P1.2 / ICAPB4	H2	P1.8 / OCMPA0 / INT0
E3	P0.10 / OCMPA7	F3	P0.14 / OCMPB3	G3	P1.3 / ICAPA4	H3	P1.9 / OCMPB0 / INT1
E4	P0.11 / OCMPB7	F4	P0.15 / OCMPA3	G4	V_{SS}	H4	P1.10 / ICAPB0 / WUP28
E5	P0.12 / ICAPA3	F5	P1.0 / OCMPA4	G5	P1.5	H5	XTAL2
E6	P6.5 / WUP5	F6	P1.1 / OCMPB4	G6	P2.11 / WUP17	H6	P2.10 / WUP16
E7	P6.0 / WUP0	F7	P6.1 / WUP1	G7	P4.0 / ICAPA7 / WUP24	H7	P2.15 / SDA 0
E8	P5.13 / INT11	F8	P4.4 / CAN2TX[1)]	G8	VDD	H8	JTMS
E9	P4.10 / ICAPA6 / WUP20	F9	P4.3 / ICAPB8 / WUP27	G9	VSS	H9	VSS
E10	P4.9 / ICAPB6	F10	P4.2 / ICAPA8 / WUP26	G10	JTDO	H10	VDD
E11	P4.6 / SCL1 / WUP19	F11	P4.1 / ICAPB7 / WUP25	G11	JTCK	H11	P3.15 / AIN15 / INT5
E12	P4.5 / WUP18 / CAN2RX[1)]	F12	JTDI	G12	nJTRST	H12	P3.14 / AIN14 / INT4
J1	P1.4	K1	P1.6 / OCMPB1	L1	P1.7 / OCMPA1	M1	P1.14 / CAN0RX[1)] / WUP12
J2	P1.11 / ICAPA0 / WUP29	K2	P1.13 / ICAPB1 / WUP31	L2	P1.15 / CAN0TX[1)]	M2	P2.4 / PWM2
J3	P1.12 / ICAPA1 / WUP30	K3	P2.1 / CAN1RX[1)] / WUP13	L3	P2.0 / PWM0	M3	P2.5 / PWM3
J4	P2.7 / PWM5	K4	P2.6 / PWM4	L4	P2.3 / PWM1	M4	P2.2 / CAN1TX[1)]
J5	V_{DD}	K5	M1	L5	RSTIN	M5	M0
J6	P2.9 / RDI1 / WUP14	K6	P2.8 / TDO1	L6	V_{SS}	M6	V_{SS}
J7	P2.14 / SCL 0 / WUP15	K7	P2.13 / INT15	L7	P2.12 / INT14	M7	XTAL1
J8	P3.1 / AIN1	K8	P3.0 / AIN0	L8	VBIAS	M8	TST
J9	P3.13 / AIN13 / INT3	K9	P3.4 / AIN4	L9	P3.3 / AIN3	M9	P3.2 / AIN2
J10	P3.12 / AIN12 / INT2	K10	V_{DDA}	L10	P3.5 / AIN5	M10	V_{SS}
J11	P3.9 / AIN9	K11	V_{SSA}	L11	P3.7 / AIN7	M11	V_{DD}
J12	P3.8 / AIN8	K12	P3.11 / AIN11	L12	P3.10 / AIN10	M12	P3.6 / AIN6

Note: CAN alternate functions not available on STR735F.

Legend / Abbreviations for *Table 4*:

Type: I = input, O = output, S = supply, HiZ= high impedance,

In/Output level: T_T= TTL 0.8 V / 2 V with input trigger
C_T= CMOS $0.3V_{DD}/0.7V_{DD}$ with input trigger

Port and control configuration:

Input: pu/pd = with internal 100 kΩ weak pull-up or pull down

Output: OD = open drain (logic level)
PP = push-pull

Interrupts:

INTx = external interrupt line

WUPx = wake-up interrupt line

The reset state (during and just after the reset) of the I/O ports is input floating (Input tristate TTL mode). To avoid excess power consumption, unused I/O ports must be tied to ground.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
1	A1	1	P0.0/OCMPB2	I/O	T_T			2mA	X	X	Port 0.0	TIM2: output compare B output
2	B2	2	P0.1/OCMPA2	I/O	T_T			2mA	X	X	Port 0.1	TIM2: output compare A output
3	C2	3	P0.2/ICAPA2	I/O	T_T			2mA	X	X	Port 0.2	TIM2: input capture A input
4	C3	4	P0.3/ICAPB2	I/O	T_T			2mA	X	X	Port 0.3	TIM2: input capture B input
5	D1		V_{SS}	S							Ground	
6	D2		V_{DD}	S							Supply voltage (5 V)	
7	B1	5	P0.4/OCMPA5	I/O	T_T			2mA	X	X	Port 0.4	TIM5: output compare A output
8	C1	6	P0.5/OCMPB5	I/O	T_T			2mA	X	X	Port 0.5	TIM5: output compare B output
9	D3	7	P0.6/ICAPA5	I/O	T_T			2mA	X	X	Port 0.6	TIM5: input capture A input
10	D4		P0.7/ICAPB5	I/O	T_T			2mA	X	X	Port 0.7	TIM5: input capture B input
11	E1		P0.8/OCMPA6	I/O	T_T			2mA	X	X	Port 0.8	TIM6: output compare A output
12	E2		P0.9/OCMPB6	I/O	T_T			2mA	X	X	Port 0.9	TIM6: output compare B output
13	E3		P0.10/OCMPA7	I/O	T_T			2mA	X	X	Port 0.10	TIM7: output compare A output
14	E4		P0.11/OCMPB 7	I/O	T_T			2mA	X	X	Port 0.11	TIM7: output compare B output
15	F1	8	V_{DD}	S							Supply voltage (5 V)	
16	G1	9	V_{SS}	S							Ground	
17	E5	10	P0.12/ICAPA3	I/O	T_T			2mA	X	X	Port 0.12	TIM3: input capture A input
18	F2	11	P0.13/ICAPB3	I/O	T_T			2mA	X	X	Port 0.13	TIM3: input capture B input

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
73	M12	51	P3.6/AIN6	I/O	T_T			2mA	X	X	Port 3.6	ADC: analog input 6 (AIN2 in TQFP100)
74	L11	52	P3.7/AIN7	I/O	T_T			2mA	X	X	Port 3.7	ADC: analog input 7 (AIN3 in TQFP100)
75	K11	53	V_{SSA}	S							Reference ground for A/D converter	
76	K10	54	V_{DDA}	S							Reference voltage for A/D converter	
77	J12	55	P3.8/AIN8	I/O	T_T			2mA	X	X	Port 3.8	ADC: analog input 8 (AIN4 in TQFP100)
78	J11	56	P3.9/AIN9	I/O	T_T			2mA	X	X	Port 3.9	ADC: analog input 9 (AIN5 in TQFP100)
79	L12	57	P3.10/AIN10	I/O	T_T			2mA	X	X	Port 3.10	ADC: analog input 10 (AIN6 in TQFP100)
80	K12	58	P3.11/AIN11	I/O	T_T			2mA	X	X	Port 3.11	ADC: analog input 11 (AIN7 in TQFP100)
81	J10	59	P3.12/AIN12	I/O	T_T		INT2	2mA	X	X	Port 3.12	ADC: analog input 12 (AIN8 in TQFP100)
82	J9	60	P3.13/AIN13	I/O	T_T		INT3	2mA	X	X	Port 3.13	ADC: analog input 13 (AIN9 in TQFP100)
83	H12	61	P3.14/AIN14	I/O	T_T		INT4	2mA	X	X	Port 3.14	ADC: analog input 14 (AIN10 in TQFP100)
84	H11	62	P3.15/AIN15	I/O	T_T		INT5	2mA	X	X	Port 3.15	ADC: analog input 15 (AIN11 in TQFP100)
85	H10	63	V_{DD}	S							Supply voltage (5 V)	
86	H9	64	V_{SS}	S							Ground	
87	G12	65	JTRST	I	T_T	pu						JTAG reset Input
88	F12	66	JTDI	I	T_T	pu						JTAG data input
89	H8	67	JTMS	I	T_T	pu						JTAG mode selection Input
90	G11	68	JTCK	I	T_T	pd						JTAG clock Input
91	G10	69	JTDO	O				4mA				JTAG data output. **Note:** Reset state = HiZ
92	G9	70	V_{SS}	S								Ground
93	G8	71	V_{DD}	S								Supply voltage (5 V)
94	G7		P4.0/ICAPA7	I/O	T_T		WUP24	2mA	X	X	Port 4.0	TIM7: input capture A input
95	F11		P4.1/ICAPB7	I/O	T_T		WUP25	2mA	X	X	Port 4.1	TIM7: input capture B input
96	F10		P4.2/ICAPA8	I/O	T_T		WUP26	2mA	X	X	Port 4.2	TIM8: input capture A input

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
97	F9		P4.3/ICAPB8	I/O	T_T		WUP27	2mA	X	X	Port 4.3	TIM8: input capture B input	
98	F8		P4.4/CAN2TX	I/O	T_T			2mA	X	X	Port 4.4	CAN2: transmit data output	
99	E12		P4.5/CAN2RX	I/O	T_T		WUP18	2mA	X	X	Port 4.5	CAN2: receive data input	
100	E11	72	P4.6/SCL1	I/O	T_T		WUP19	2mA	X	X	Port 4.6	I2C1: serial clock	
101	C12	73	P4.7/SDA1	I/O	T_T			2mA	X	X	Port 4.7	I2C1: serial data	
102	B12		P4.8/OCMPA8	I/O	T_T			2mA	X	X	Port 4.8	TIM8: output compare A output	
103	E10		P4.9/ICAPB6	I/O	T_T			2mA	X	X	Port 4.9	TIM6: input capture B input	
104	E9	74	P4.10/ICAPA6/ICAPB5	I/O	T_T		WUP20	2mA	X	X	Port 4.10	TIM6: input capture A input (144-pin pkg only)	TIM5: input capture B input (TQFP100 only)
105	D12		P4.11/OCMPB8	I/O	T_T			2mA	X	X	Port 4.11	TIM8: output compare B output	
106	D11		P4.12/ICAPA9	I/O	T_T		WUP21	2mA	X	X	Port 4.12	TIM9: input capture A input	
107	D10		P4.13/ICAPB9	I/O	T_T			2mA	X	X	Port 4.13	TIM9: input capture B input	
108	C11	75	P4.14/$\overline{SS}$1	I/O	T_T			2mA	X	X	Port 4.14	BSPI1: slave select	
109	B11	76	P4.15/SCK1	I/O	T_T		WUP22	2mA	X	X	Port 4.15	BSPI1: serial clock	
110	B10	77	P5.0/MOSI1	I/O	T_T			2mA	X	X	Port 5.0	BSPI1: master output/slave input	
111	C10	78	P5.1/MISO1	I/O	T_T			2mA	X	X	Port 5.1	BSPI1: master input/Slave output	
112	A9		P5.2/OCMPA9	I/O	T_T			2mA	X	X	Port 5.2	TIM9: output compare A output	
113	B9		P5.3/OCMPB9	I/O	T_T			2mA	X	X	Port 5.3	TIM9: output compare B output	
114	C9	79	P5.4/$\overline{SS}$2/PWM3	I/O	T_T			2mA	X	X	Port 5.4	BSPI2: slave select	PWM3: PWM output (TQFP100 only)
115	D9	80	P5.5/SCK2	I/O	T_T		WUP23	2mA	X	X	Port 5.5	BSPI2: serial clock	
116	A11	81	P5.6/MOSI2	I/O	T_T			2mA	X	X	Port 5.6	BSPI2: master output/slave input	
117	A10	82	P5.7/MISO2	I/O	T_T			2mA	X	X	Port 5.7	BSPI2: master input/slave output	
118	A8	83	P5.8/PWM4	I/O	T_T		INT6	2mA	X	X	Port 5.8	PWM4: PWM output (TQFP100 only)	

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
119	B8	84	P5.9/PWM5	I/O	T_T		INT7	2mA	X	X	Port 5.9	PWM5: PWM output (TQFP100 only)
120	C8	85	P5.10/RDI2	I/O	T_T		INT8	2mA	X	X	Port 5.10	UART2: receive data input
121	A12	86	P5.11/TDO2	I/O	T_T		INT9	2mA	X	X	Port 5.11	UART2: transmit data output
122	D8	87	P5.12	I/O	T_T		INT10	2mA	X	X	Port 5.12	
123	E8		P5.13	I/O	T_T		INT11	2mA	X	X	Port 5.13	
124	B7		P5.14	I/O	T_T		INT12	2mA	X	X	Port 5.14	
125	A7		P5.15	I/O	T_T		INT13	2mA	X	X	Port 5.15	
126	A6	88	V_{18}	S								1.8 V decoupling pin: a decoupling capacitor (recommended value: 100 nF) must be connected between this pin and nearest VSS pin.
127	C7	89	V_{SS}	S								Ground
128	D7	90	V_{DD}	S								Supply voltage (5 V)
129	E7	91	P6.0	I/O	T_T		WUP0	8mA	X	X	Port 6.0	
130	F7		P6.1	I/O	T_T		WUP1	2mA	X	X	Port 6.1	
131	B6	92	P6.2/RDI3	I/O	T_T		WUP2	2mA	X	X	Port 6.2	UART3: receive data input
132	C6		P6.3	I/O	T_T		WUP3	2mA	X	X	Port 6.3	
133	D6	93	P6.4/TDO3	I/O	T_T		WUP4	2mA	X	X	Port 6.4	UART3: transmit data output
134	E6		P6.5	I/O	T_T		WUP5	2mA	X	X	Port 6.5	
135	A5	94	P6.6	I/O	T_T		WUP6	2mA	X	X	Port 6.6	
136	B5		P6.7	I/O	T_T		WUP7	2mA	X	X	Port 6.7	
137	C5	95	P6.8/RDI0	I/O	T_T		WUP10	2mA	X	X	Port 6.8	UART0: receive data input
138	A3	96	P6.9/TDO0	I/O	T_T			2mA	X	X	Port 6.9	UART0: transmit data output
139	A2		P6.10	I/O	T_T		WUP8	2mA	X	X	Port 6.10	
140	D5	97	P6.11/MISO0	I/O	T_T			2mA	X	X	Port 6.11	BSPI0: master input/slave output
141	A4	98	P6.12/MOSI0	I/O	T_T			2mA	X	X	Port 6.12	BSPI0: master output/slave input
142	B4	99	P6.13/SCK0	I/O	T_T		WUP11	2mA	X	X	Port 6.13	BSPI0: serial clock
143	C4	100	P6.14/$\overline{SS}$0	I/O	T_T			2mA	X	X	Port 6.14	BSPI0: slave select
144	B3		P6.15	I/O	T_T		WUP9	2mA	X	X	Port 6.15	

4 Electrical parameters

4.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

4.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A=25° C and T_A=T_{Amax} (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

4.1.2 Typical values

Unless otherwise specified, typical data are based on T_A=25° C and V_{DD}=5 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

4.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

4.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

4.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

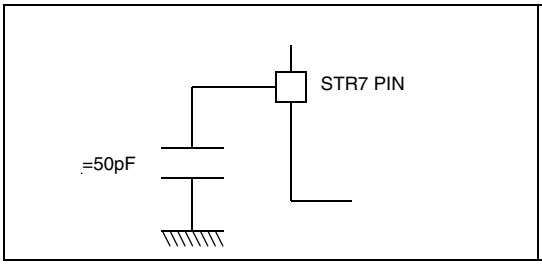
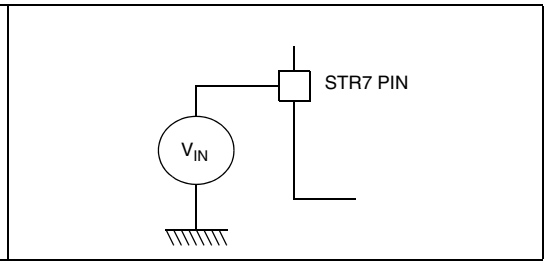


Figure 7. Pin input voltage



Main oscillator characteristics

V_{DD} = 5 V ± 10%, T_A = -40° C to T_{Amax}, unless otherwise specified.

Table 14. Main oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{OSC}	Oscillator frequency		4		8	MHz
g_m	Oscillator transconductance		1.5		4.2	mA/V
V_{OSC} 1)	Oscillation amplitude	f_{OSC} = 4 MHz, T_A= 25° C	-	2.4	-	V
		f_{OSC} = 8 MHz, T_A= 25° C		1.-		
V_{AV} 1)	Oscillator operating point	Sine wave middle, T_A= 25° C	-	0.77	-	v
t_{STUP} 1)	Oscillator start-up time	External crystal, V_{DD} = 5.5 V, f_{OSC} = 4 MHz, T_A=-40° C	-	-	12	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 4 MHz, T_A=25° C	-	5.5	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 6 MHz, T_A=-40° C	-	-	8	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 6 MHz, T_A=25° C	-	3.3	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 8 MHz, T_A=-40° C	-	-	7	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 8 MHz, T_A= 25° C	-	2.7	-	ms

Table 14. Main oscillator characteristics (continued)

Symbol	Parameter	Conditions		Value			Unit
				Min	Typ	Max	
R_F [1]	Feedback resistor	f_{OSC} = 4 MHz Cp[2] = 10 pF	C_1[3] = C_2 [4]= 10 pF	150	555	-	Ω
			$C_1 = C_2$ = 20 pF	490	1035	-	
			$C_1 = C_2$ = 30 pF	490	1030	-	
			$C_1 = C_2$ = 40 pF	380	850	-	
		f_{OSC} = 5 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	470	-	
			$C_1 = C_2$ = 20 pF	415	800	-	
			$C_1 = C_2$ = 30 pF	340	735	-	
			$C_1 = C_2$ = 40 pF	260	580	-	
		f_{OSC} = 6 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	415	-	
			$C_1 = C_2$ = 20 pF	325	640	-	
			$C_1 = C_2$ = 30 pF	250	550	-	
			$C_1 = C_2$ = 40 pF	180	420	-	
		f_{OSC} = 7 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	160	375	-	
			$C_1 = C_2$ = 20 pF	260	525	-	
			$C_1 = C_2$ = 30 pF	185	420	-	
			$C_1 = C_2$ = 40 pF	135	315	-	
		f_{OSC} = 8 MHz Cp = 10 pF	$C_1 = C_2$ = 10 pF	155	340	-	
			$C_1 = C_2$ = 20 pF	210	435	-	
			$C_1 = C_2$ = 30 pF	145	335	-	
			$C_1 = C_2$ = 40 pF	100	245	-	

1. Min and max values are guaranteed by characterization, not tested in production.
2. C_P represents the total capacitance between XTAL1 and XTAL2, including the shunt capacitance of the external quartz crystal as well as the total board parasitic cross-capacitance between XTAL1 track and XTAL2 track.
3. C_1 represents the total capacitance between XTAL1 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL1 track and ground (this includes application board track capacitance to ground and device pin capacitance).
4. C_2 represents the total capacitance between XTAL2 and ground, including the external capacitance tied to XTAL1 pin (C_L) as well as the total parasitic capacitance between XTAL2 track and ground (this includes application board track capacitance to ground and device pin capacitance).

4.3.3 Memory characteristics

Flash memory

Table 18. Flash memory characteristics

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typ	Max[1)]	
t_{WP}	Word program (32-bit)			35	80	µs
t_{DWP}	Double word program(64-bit)			64	150	µs
t_{BP64}	Bank program (64 K)	Double word program		0.5	1.25	s
t_{BP128}	Bank program (128 K)	Double word program		1	2.5	s
t_{BP256}	Bank program (256 K)	Double word program		2	4.9	s
t_{SE8}	Sector erase (8 K)	Not preprogrammed Preprogrammed [2)]		0.6 0.5	0.9 0.8	s
t_{SE32}	Sector erase (32 K)	Not preprogrammed Preprogrammed[2)]		1.1 0.8	2 1.8	s
t_{SE64}	Sector erase (64 K)	Not preprogrammed preprogrammed [2)]		1.7 1.3	3.7 3.3	s
t_{RPD}[3)]	Recovery from power-down				20	µs
t_{PSL}[3)]	Program suspend latency				10	µs
t_{ESL}[3)]	Erase suspend latency				30	µs
t_{ESR}[3)]	Erase suspend rate	Min. time from erase resume to next erase suspend		20	20	ms
t_{SP}[3)]	Set protection			40	170	µs
t_{FPW}[3)]	First word program			1		ms
N_{END}	Endurance		10			kcycles
t_{RET}	Data retention	T_A = 85° C	20			Years

1. T_A = -45° C after 0 cycles, Guaranteed by characterization, not tested in production.
2. All bits programmed to 0.
3. Guaranteed by design, not tested in production.

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-4	4A

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 20. EMI data

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{OSC4M}/f_{MCLK}]		Unit
				6/36 MHz	8/8 MHz	
S_{EMI}	Peak level	V_{DD}=5.0V, T_A=+25°C, All packages	0.1 MHz to 30 MHz	23	30	dBµV
			30 MHz to 130 MHz	37	34	
			130 MHz to 1 GHz	20	7	
			SAE EMI Level	4	3.5	-

Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: human body model and machine model. This test conforms to the JESD22-A114A/A115A standard.

Table 21. ESD Absolute Maximum ratings

Symbol	Ratings	Conditions	Maximum value [1]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A=+25° C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (machine model)		200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)		750 on corner pins, 500 on others	

Notes:

1. Data based on characterization results, not tested in production.

Static and dynamic latch-up

- **LU**: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each

sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

- **DLU**: Electrostatic discharges (one positive then one negative test) are applied to each pin of 3 samples when the micro is running to assess the latch-up performance in dynamic mode. Power supplies are set to the typical values, the oscillator is connected as near as possible to the pins of the micro and the component is put in reset mode. This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details, refer to the application note AN1181.

Table 22. Electrical sensitivities

Symbol	Parameter	Conditions	Class [1]
LU	Static latch-up class	T_A=+25°C T_A=+85°C T_A=+105°C	A A A
DLU	Dynamic latch-up class	V_{DD}= 5.5 V, f_{OSC4M} = 4 MHz, f_{MCLK} = 32 MHz, T_A = +25° C	A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

4.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 23. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage [1]	TTL ports			0.8	V
V_{IH}	Input high level voltage [1]		2.0			
$I_{INJ(PIN)}$	Injected current on any I/O pin				±10	mA
$\Sigma I_{INJ(PIN)}$ [2]	Total injected current (sum of all I/O and control pins)				±75	mA
I_{lkg}	Input leakage current [3]	$V_{SS} \leq V_{IN} \leq V_{DD}$			±1	µA
I_S	Static current consumption [4]	Floating input mode		200		µA
R_{PU}	Weak pull-up equivalent resistor[5]	$V_{IN}=V_{SS}$	55	120	220	kΩ
R_{PD}	Weak pull-down equivalent resistor[5]	$V_{IN}=V_{DD}$	55	120	220	kΩ
C_{IO}	I/O pin capacitance			5		pF

1. Data based on characterization results, not tested in production.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN}>V_{33}$ while a negative injection is induced by $V_{IN}<V_{SS}$. Refer to *Section 4.2 on page 22* for more details.
3. Leakage could be higher than max. if negative current is injected on adjacent pins.
4. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor. Data based on design simulation and/or technology characteristics, not tested in production.
6. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in *Figure 19*).

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 24. Output driving current

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Standard	V_{OL} 1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO}=+2 mA		0.4	V
	V_{OH} 2)	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I_{IO}=-2 mA	V_{DD}-0.8		
Med. Current (JTDO)	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+6 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-6 mA	V_{DD}-0.8		
High Current P6.0	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+8 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-8 mA	V_{DD}-0.8		

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed IV_{DD}.

Figure 13. V_{OH} standard ports vs I_{OH} @ V_{DD} 5V T_A -45° C

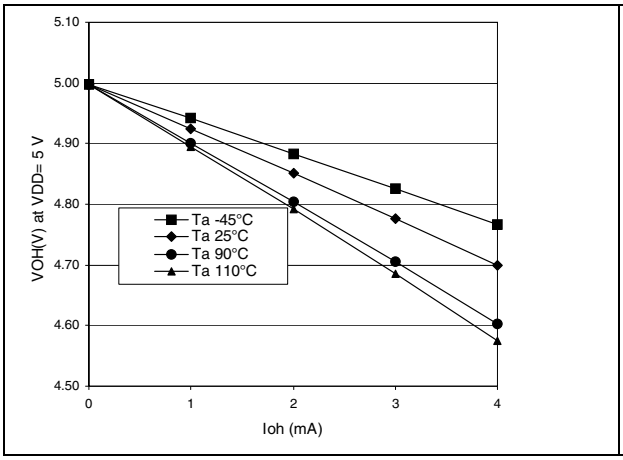


Figure 14. V_{OL} standard ports vs I_{OL} @ V_{DD} 5 V

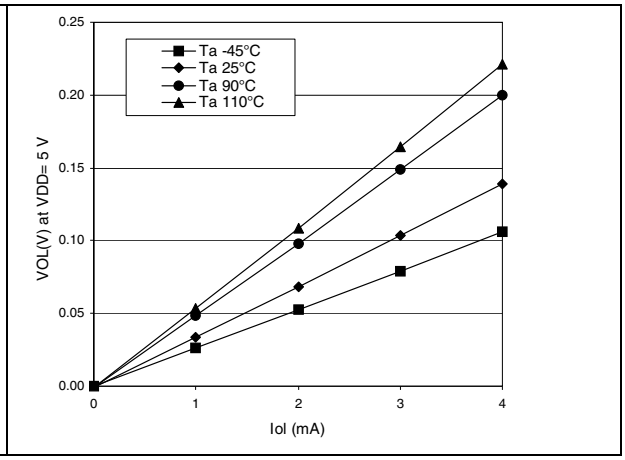


Figure 15. V_{OH} JTDO pin vs I_{OL} @ V_{DD} 5 V

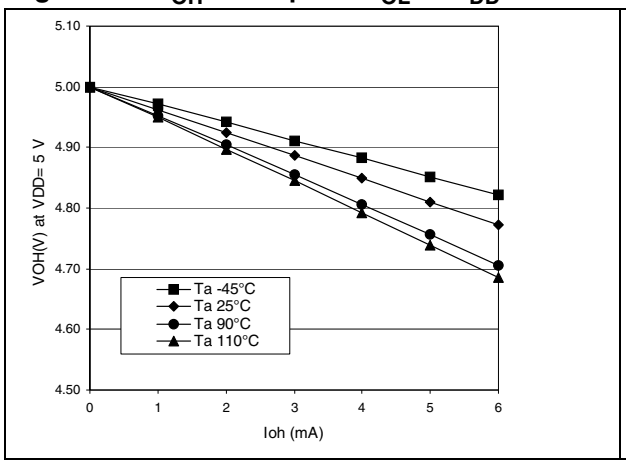


Figure 16. V_{OL} JTDO pin vs I_{OL} @ V_{DD} 5 V

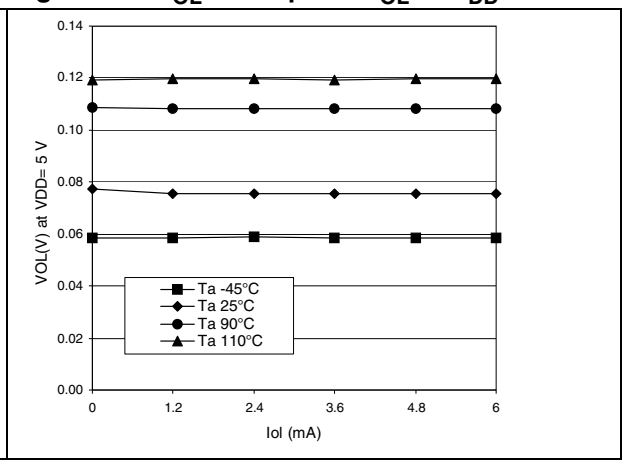


Figure 17. V_{OH} P6.0 pin vs I_{OL} @ V_{DD} 5 V

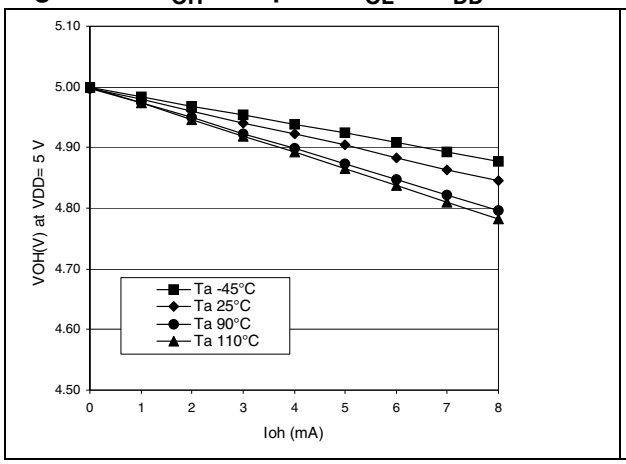


Figure 18. V_{OL} P6.0 pin vs I_{OL} @ V_{DD} 5 V

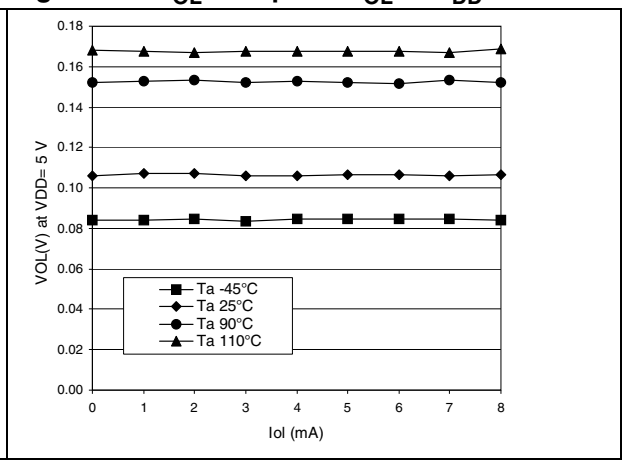


Table 27. ADC accuracy with f_{MCLK} = 20 MHz, f_{ADC}=10 MHz, R_{AIN} < 10 kΩ RAIN, V_{DDA}=5 V. This assumes that the ADC is calibrated[2)]

Symbol	Parameter	Conditions	Typ	Max	Unit
$\|E_T\|$	Total unadjusted error [1)]		1.0	2.0	LSB
$\|E_O\|$	Offset error [1)]		0.15	1.0	
$\|E_G\|$	Gain error [1)]		0.97	1.1	
$\|E_D\|$	Differential linearity error[1)]		0.7	1.0	
$\|E_L\|$	Integral linearity error [1)]		0.76	1.5	

1. ADC accuracy vs. negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. The effect of negative injection current on robust pins is specified in *Section 4.3.5*.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 4.3.5* does not affect the ADC accuracy.
2. Calibration is needed once after each power-up.

Figure 21. ADC accuracy characteristics

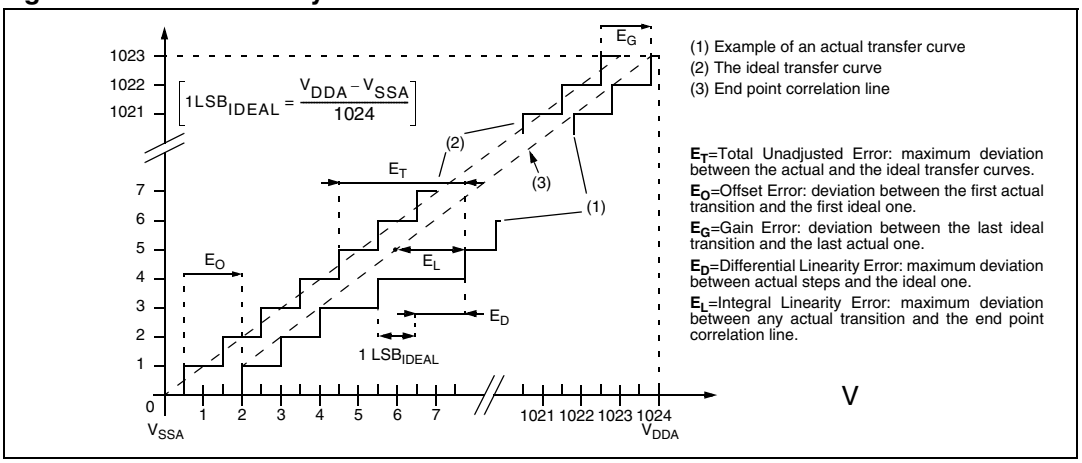
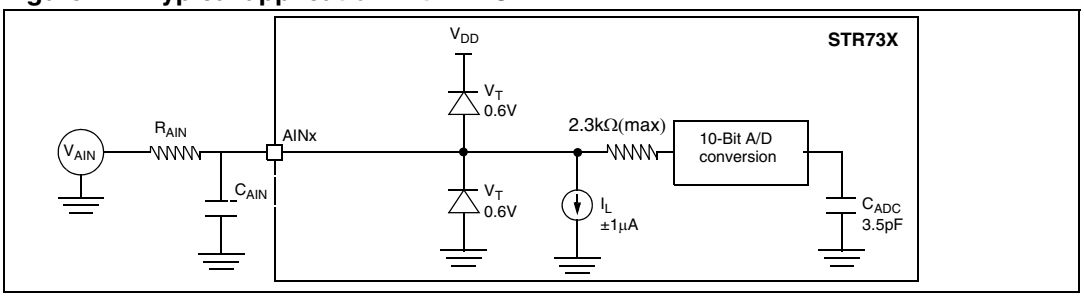


Figure 22. Typical application with ADC



6 Order codes

Table 29. Order codes

Partnumber	Flash Kbytes	Package	RAM Kbytes	TIM timers	6x PWM module	CAN periph	A/D chan.	Wake-up lines	I/O ports	Temp. range
STR730FZ1T6	128	TQFP144 20x20	16	10	1	3	16	32	112	-40 to +85°C
STR730FZ2T6	256									
STR730FZ1H6	128	LFBGA144 10x10								
STR730FZ2H6	256									
STR735FZ1T6	128	TQFP144 20x20				0				
STR735FZ2T6	256									
STR735FZ1H6	128	LFBGA144 10x10								
STR735FZ2H6	256									
STR731FV0T6	64	TQFP100 14x14		6		3	12	18	72	
STR731FV1T6	128									
STR731FV2T6	256									
STR736FV0T6	64	TQFP100 14x14				0				
STR736FV1T6	128									
STR736FV2T6	256									
STR730FZ1T7	128	TQFP144 20x20	16	10	1	3	16	32	112	-40 to +105°C
STR730FZ2T7	256									
STR730FZ1H7	128	LFBGA144 10x10								
STR730FZ2H7	256									
STR735FZ1T7	128	TQFP144 20x20				0				
STR735FZ2T7	256									
STR735FZ1H7	128	LFBGA144 10x10								
STR735FZ2H7	256									
STR731FV0T7	64	TQFP100 14x14		6		3	12	18	72	
STR731FV1T7	128									
STR731FV2T7	256									
STR736FV0T7	64	TQFP100 14x14				0				
STR736FV1T7	128									
STR736FV2T7	256									

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